

NXH80B120H2Q0

Dual Boost Power Module

The NXH80B120H2Q0 is a high-density, integrated power module combines high-performance IGBTs with rugged anti-parallel diodes including on-board thermistor.

Features

- Dual Boost 40 A / 1200 V IGBT + SiC Rectifier Hybrid Module
- 1200 V FSII IGBT $V_{CE(SAT)} = 2.2\text{ V}$
- 1200 V SiC Diode $V_F = 1.4\text{ V}$
- Low Inductive Layout
- Solderable Pins
- Thermistor
- Bare Copper and Nickel-Plated DBC Options

Typical Applications

- Solar Inverter
- Uninterruptible Power Supplies
- Energy Storage Systems

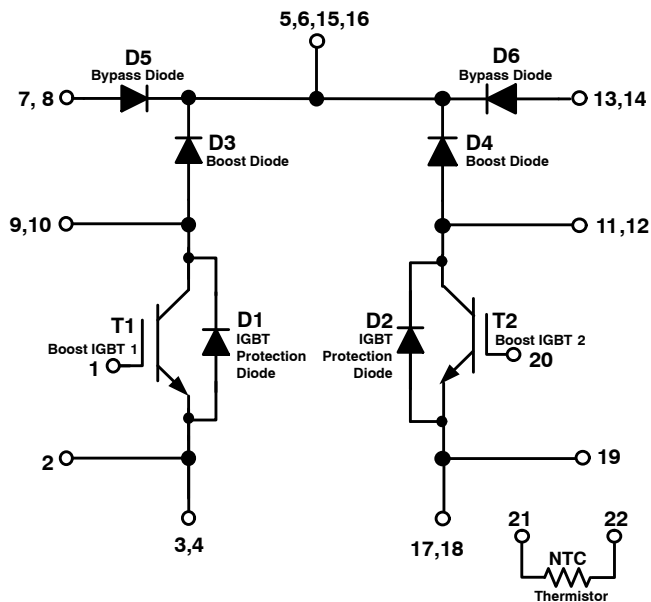
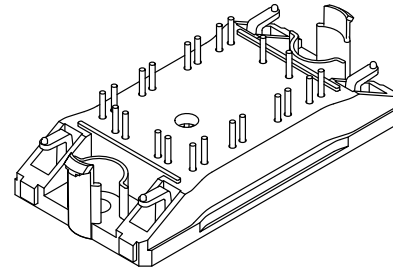


Figure 1. NXH80B120H2Q0SG Schematic Diagram



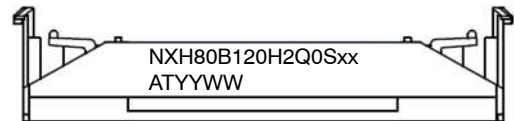
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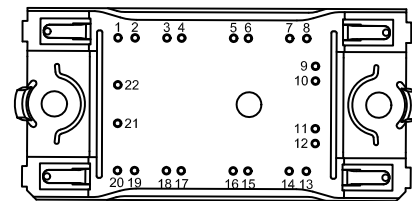
Q0BOOST
CASE 180AJ

MARKING DIAGRAM



NXH80B120H2Q0Sxx = Device Code
AT = Assembly & Test Site Code
YYWW = Year and Work Week Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 4 of this data sheet.

NXH80B120H2Q0

Table 1. ABSOLUTE MAXIMUM RATINGS (Note 1) $T_J = 25^\circ\text{C}$ unless otherwise noted

| Rating | Symbol | Value | Unit |
|--|--------------|----------|------------------|
| BOOST IGBT | | | |
| Collector-Emitter Voltage | V_{CES} | 1200 | V |
| Gate-Emitter Voltage | V_{GE} | ± 20 | V |
| Continuous Collector Current @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | I_C | 41 | A |
| Pulsed Collector Current ($T_J = 175^\circ\text{C}$) | I_{Cpulse} | 123 | A |
| Maximum Power Dissipation @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | P_{tot} | 103 | W |
| Short Circuit Withstand Time @ $V_{GE} = 15\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J \leq 150^\circ\text{C}$ | T_{sc} | 5 | μs |
| Minimum Operating Junction Temperature | T_{JMIN} | -40 | $^\circ\text{C}$ |
| Maximum Operating Junction Temperature | T_{JMAX} | 150 | $^\circ\text{C}$ |

| | | | |
|---|------------|------|----------------------|
| BOOST DIODE | | | |
| Peak Repetitive Reverse Voltage | V_{RRM} | 1200 | V |
| Continuous Forward Current @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | I_F | 28 | A |
| Repetitive Peak Forward Current (limited by T_J , duty cycle = 10%) | I_{FRM} | 75 | A |
| Maximum Power Dissipation @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | P_{tot} | 79 | W |
| Surge Forward Current (60 Hz single half-sine wave) ($T_J = 25^\circ\text{C}$) | I_{FSM} | 69 | A |
| I^2t - value (60 Hz single half-sine wave) ($T_J = 150^\circ\text{C}$) | I^2t | 19 | A^2s |
| Minimum Operating Junction Temperature | T_{JMIN} | -40 | $^\circ\text{C}$ |
| Maximum Operating Junction Temperature | T_{JMAX} | 150 | $^\circ\text{C}$ |

| | | | |
|---|------------|------|------------------|
| BYPASS DIODE / IGBT PROTECTION DIODE | | | |
| Peak Repetitive Reverse Voltage | V_{RRM} | 1600 | V |
| Continuous Forward Current @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | I_F | 46 | A |
| Repetitive Peak Forward Current ($T_J = 175^\circ\text{C}$, t_p limited by T_{Jmax}) | I_{FRM} | 130 | A |
| Power Dissipation Per Diode @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | P_{tot} | 66 | W |
| Minimum Operating Junction Temperature | T_{JMIN} | -40 | $^\circ\text{C}$ |
| Maximum Operating Junction Temperature | T_{JMAX} | 150 | $^\circ\text{C}$ |

THERMAL PROPERTIES

| | | | |
|---------------------------|-----------|------------|------------------|
| Storage Temperature range | T_{stg} | -40 to 125 | $^\circ\text{C}$ |
|---------------------------|-----------|------------|------------------|

INSULATION PROPERTIES

| | | | |
|--|----------|------|-----------|
| Isolation test voltage, $t = 1\text{ sec}$, 60 Hz | V_{is} | 3000 | V_{RMS} |
| Creepage distance | | 12.7 | mm |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.

Table 2. RECOMMENDED OPERATING RANGES

| Rating | Symbol | Min | Max | Unit |
|---------------------------------------|--------|-----|---------------------|------------------|
| Module Operating Junction Temperature | T_J | -40 | ($T_{jmax} - 25$) | $^\circ\text{C}$ |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

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Table 3. ELECTRICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|---------------------------------------|--|---------------|------|------|-----|--------------------|
| BOOST IGBT CHARACTERISTICS | | | | | | |
| Collector-Emitter Cutoff Current | $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$ | I_{CES} | – | – | 200 | μA |
| Collector-Emitter Saturation Voltage | $V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 25^\circ\text{C}$ | $V_{CE(sat)}$ | – | 2.20 | 2.5 | V |
| | $V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 150^\circ\text{C}$ | | – | 2.16 | – | |
| Gate-Emitter Threshold Voltage | $V_{GE} = V_{CE}, I_C = 1.5\text{ mA}$ | $V_{GE(TH)}$ | – | 5.45 | 6.4 | V |
| Gate Leakage Current | $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$ | I_{GES} | – | – | 200 | nA |
| Turn-on Delay Time | $T_J = 25^\circ\text{C}$ $V_{CE} = 700\text{ V}, I_C = 40\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4\ \Omega$ | $t_{d(on)}$ | – | 27 | – | ns |
| Rise Time | | t_r | – | 19 | – | |
| Turn-off Delay Time | | $t_{d(off)}$ | – | 94 | – | |
| Fall Time | | t_f | – | 78 | – | |
| Turn-on Switching Loss per Pulse | | E_{on} | – | 540 | – | |
| Turn-off Switching Loss per Pulse | E_{off} | – | 1640 | – | | |
| Turn-on Delay Time | $T_J = 125^\circ\text{C}$ $V_{CE} = 700\text{ V}, I_C = 40\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4\ \Omega$ | $t_{d(on)}$ | – | 27 | – | ns |
| Rise Time | | t_r | – | 20 | – | |
| Turn-off Delay Time | | $t_{d(off)}$ | – | 110 | – | |
| Fall Time | | t_f | – | 189 | – | |
| Turn-on Switching Loss per Pulse | | E_{on} | – | 620 | – | |
| Turn-off Switching Loss per Pulse | E_{off} | – | 3590 | – | | |
| Input Capacitance | $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 10\text{ kHz}$ | C_{ies} | – | 9700 | – | pF |
| Output Capacitance | | C_{oes} | – | 200 | – | |
| Reverse Transfer Capacitance | | C_{res} | – | 170 | – | |
| Total Gate Charge | $V_{CE} = 600\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$ | Q_g | – | 400 | – | nC |
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness < 100 μm , $\lambda = 0.84\text{ W/mK}$ | R_{thJH} | – | 0.92 | – | $^\circ\text{C/W}$ |

BOOST DIODE CHARACTERISTICS

| | | | | | | |
|---------------------------------------|--|------------|---|------|-----|------------------------|
| Diode Reverse Leakage Current | $V_R = 1200\text{ V}$ | I_R | – | – | 300 | μA |
| Diode Forward Voltage | $I_F = 15\text{ A}, T_J = 25^\circ\text{C}$ | V_F | – | 1.42 | 1.7 | V |
| | $I_F = 15\text{ A}, T_J = 150^\circ\text{C}$ | | – | 1.95 | – | |
| Reverse Recovery Time | $T_J = 25^\circ\text{C}$ $V_{CE} = 700\text{ V}, I_C = 40\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4\ \Omega$ | t_{rr} | – | 27 | – | ns |
| Reverse Recovery Charge | | Q_{rr} | – | 280 | – | nC |
| Peak Reverse Recovery Current | | I_{RRM} | – | 16 | – | A |
| Peak Rate of Fall of Recovery Current | | di/dt | – | 1080 | – | $\text{A}/\mu\text{s}$ |
| Reverse Recovery Energy | | E_{rr} | – | 130 | – | μJ |
| Reverse Recovery Time | $T_J = 125^\circ\text{C}$ $V_{CE} = 700\text{ V}, I_C = 40\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4\ \Omega$ | t_{rr} | – | 28 | – | ns |
| Reverse Recovery Charge | | Q_{rr} | – | 250 | – | nC |
| Peak Reverse Recovery Current | | I_{RRM} | – | 15 | – | A |
| Peak Rate of Fall of Recovery Current | | di/dt | – | 940 | – | $\text{A}/\mu\text{s}$ |
| Reverse Recovery Energy | | E_{rr} | – | 110 | – | μJ |
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness < 100 μm , $\lambda = 0.84\text{ W/mK}$ | R_{thJH} | – | 1.21 | – | $^\circ\text{C/W}$ |

BYPASS DIODE/IGBT PROTECTION DIODE CHARACTERISTICS

| | | | | | | |
|-------------------------------|---|-------|---|---|-----|---------------|
| Diode Reverse Leakage Current | $V_R = 1600\text{ V}, T_J = 25^\circ\text{C}$ | I_R | – | – | 100 | μA |
|-------------------------------|---|-------|---|---|-----|---------------|

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Table 3. ELECTRICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|---|---|------------|-----|------|-----|--------------------|
| BYPASS DIODE/IGBT PROTECTION DIODE CHARACTERISTICS | | | | | | |
| Diode Forward Voltage | $I_F = 25\text{ A}, T_J = 25^\circ\text{C}$ | V_F | – | 1.0 | 1.4 | V |
| | $I_F = 25\text{ A}, T_J = 150^\circ\text{C}$ | | – | 0.90 | – | |
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness < 100 μm , $\lambda = 0.84\text{ W/mK}$ | R_{thJH} | – | 1.44 | – | $^\circ\text{C/W}$ |

THERMISTOR CHARACTERISTICS

| | | | | | | |
|----------------------------|--------------------------------|--------------|----|------|---|------------------|
| Nominal resistance | | R_{25} | – | 22 | – | $\text{k}\Omega$ |
| Nominal resistance | $T = 100^\circ\text{C}$ | R_{100} | – | 1486 | – | Ω |
| Deviation of R25 | | $\Delta R/R$ | –5 | – | 5 | % |
| Power dissipation | | P_D | – | 200 | – | mW |
| Power dissipation constant | | | – | 2 | – | mW/K |
| B-value | B(25/50), tolerance $\pm 3\%$ | | – | 3950 | – | K |
| B-value | B(25/100), tolerance $\pm 3\%$ | | – | 3998 | – | K |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

| Orderable Part Number | Marking | Package | Shipping |
|-----------------------|------------------|---|-------------------------|
| NXH80B120H2Q0SG | NXH80B120H2Q0SG | Q0BOOST – Case 180AJ Bare Copper DBC, Solder Pins (Pb-Free and Halide-Free) | 24 Units / Blister Tray |
| NXH80B120H2Q0SNG | NXH80B120H2Q0SNG | Q0BOOST – Case 180AJ Nickel-Plated DBC, Solder Pins (Pb-Free and Halide-Free) | 24 Units / Blister Tray |

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TYPICAL CHARACTERISTICS – Boost IGBT & Boost Diode

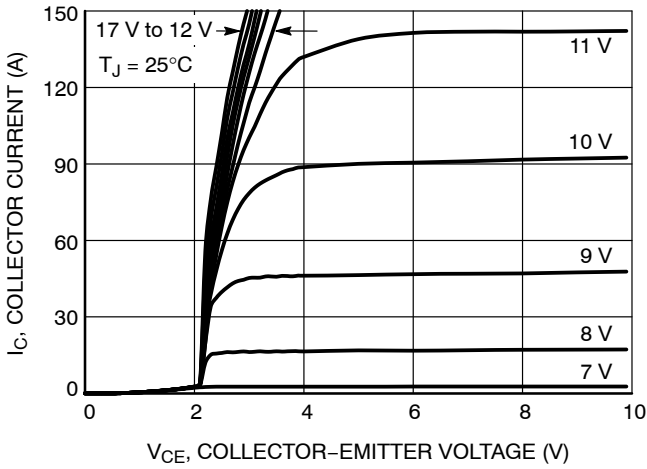


Figure 1. IGBT Typical Output Characteristics

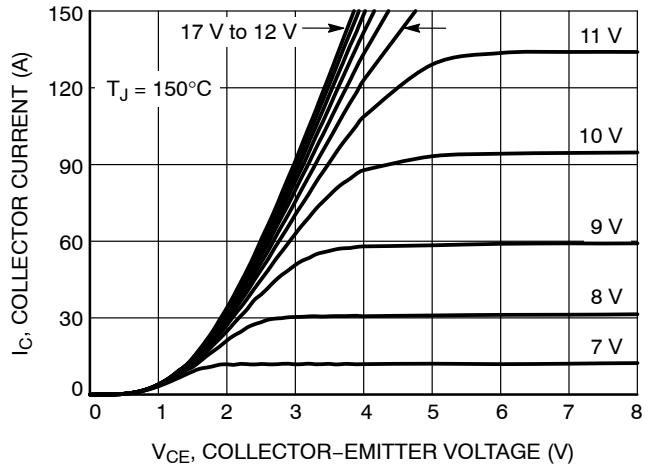


Figure 2. IGBT Typical Output Characteristics

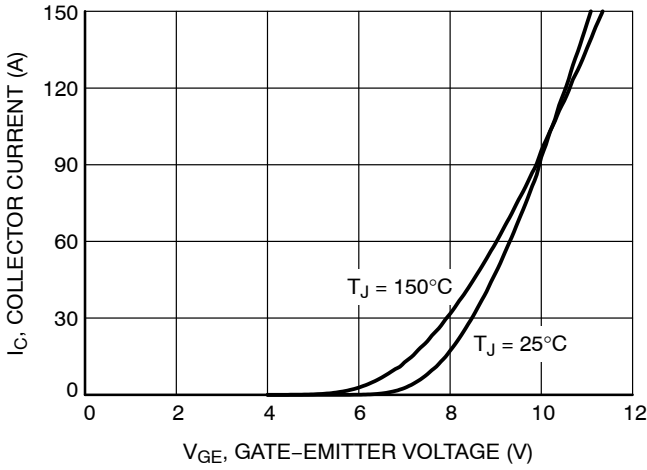


Figure 3. IGBT Typical Transfer Characteristics

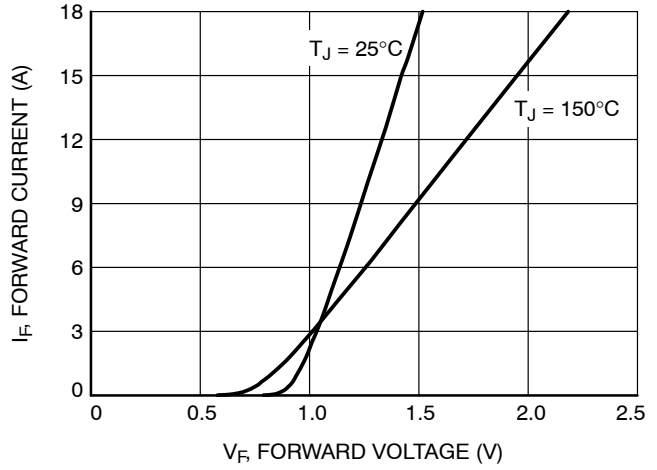


Figure 4. Diode Forward Characteristic

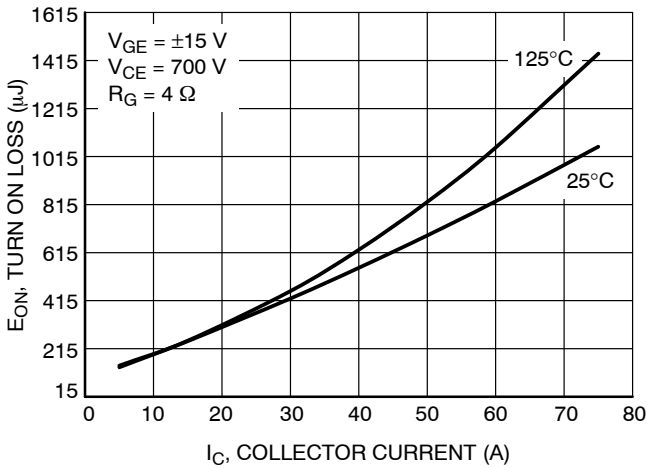


Figure 5. Typical Turn On Loss vs. Ic

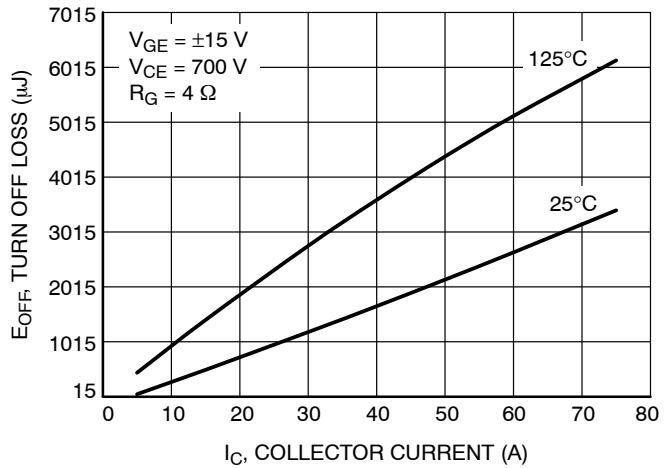


Figure 6. Typical Turn Off Loss vs. Ic

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TYPICAL CHARACTERISTICS – Boost IGBT & Boost Diode

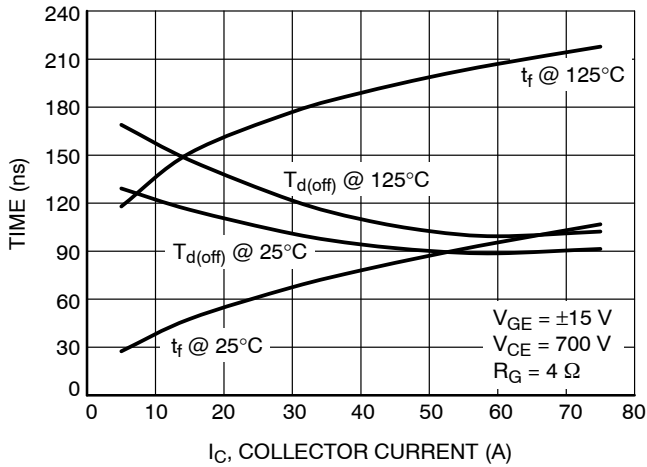


Figure 7. Typical Switching Times vs. I_C

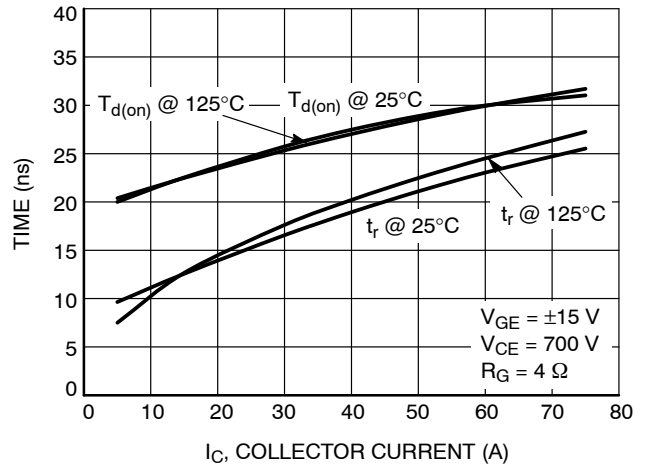


Figure 8. Typical Switching Times vs. I_C

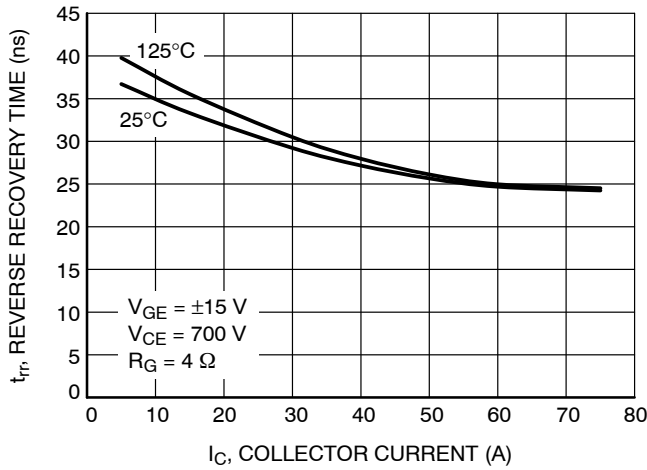


Figure 9. Typical Reverse Recovery Time vs. I_C

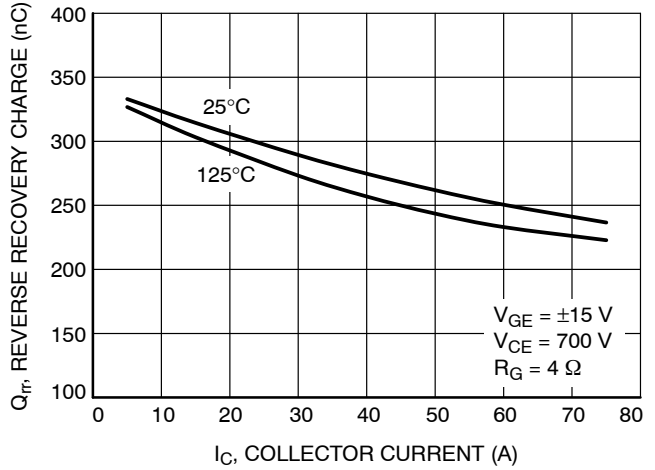


Figure 10. Typical Reverse Recovery Charge vs. I_C

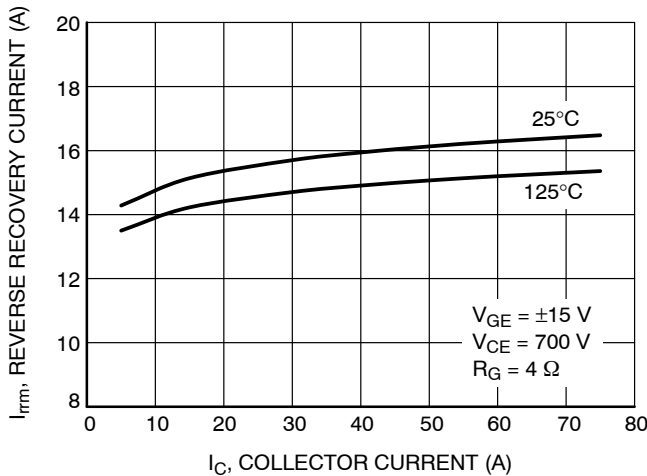


Figure 11. Typical Reverse Recovery Peak Current vs. I_C

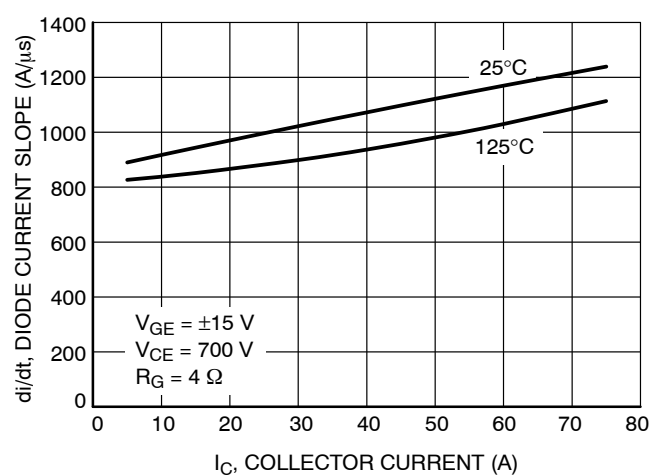


Figure 12. Typical Diode Current Slope vs. I_C

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TYPICAL CHARACTERISTICS – Boost IGBT & Boost Diode

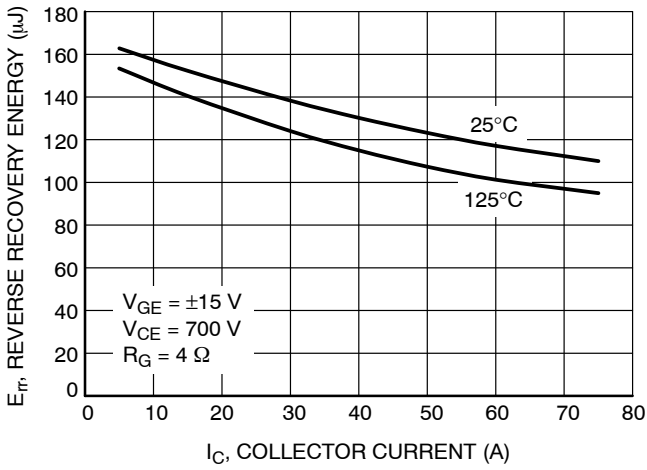


Figure 13. Typical Reverse Recovery Energy vs. I_C

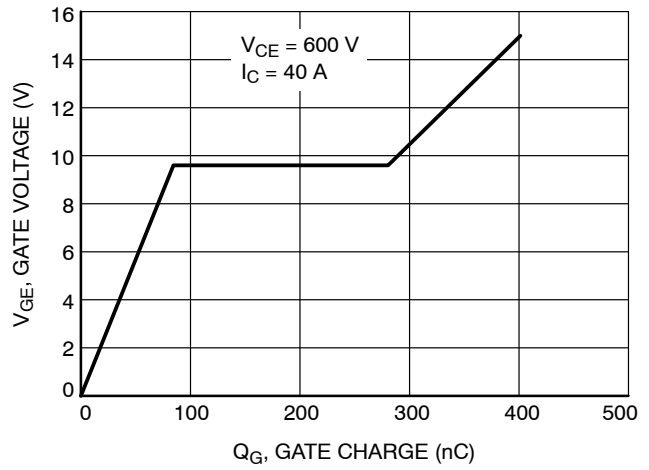


Figure 14. Gate Voltage vs. Gate Charge

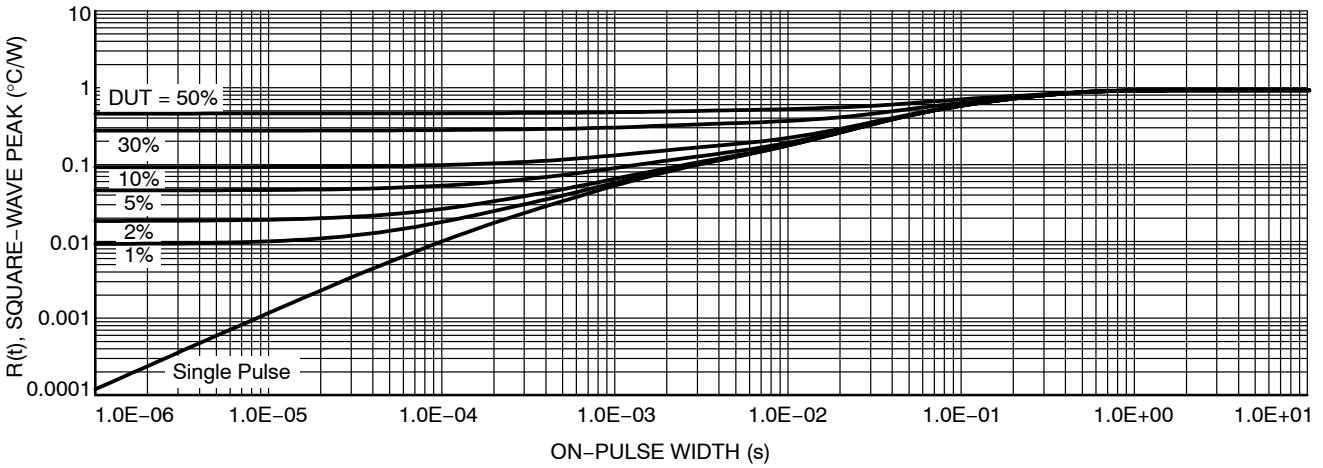


Figure 15. IGBT Transient Thermal Impedance

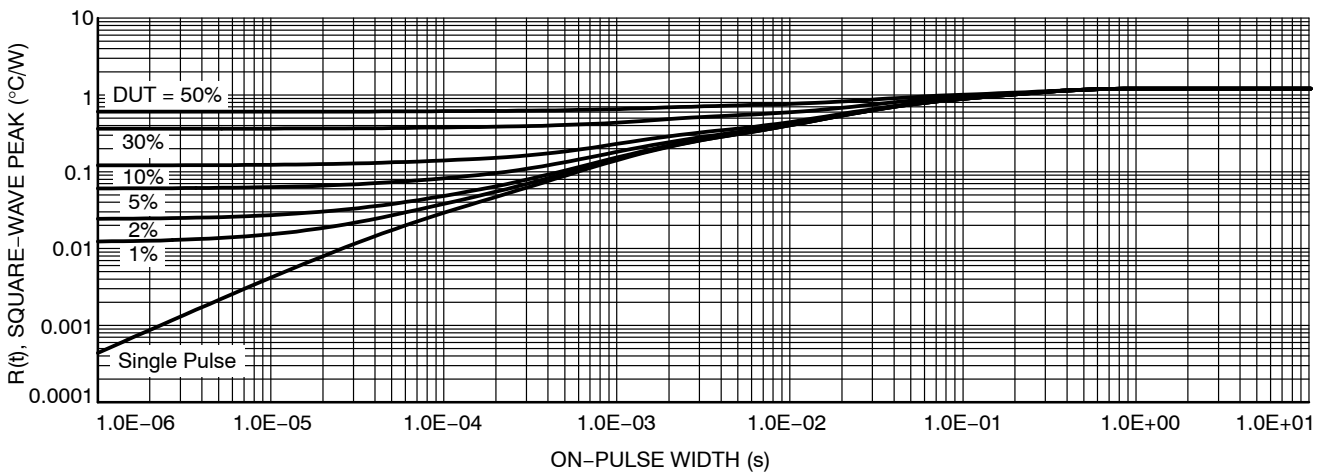


Figure 16. Diode Transient Thermal Impedance Boost Diode

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TYPICAL CHARACTERISTICS – Boost IGBT & Boost Diode

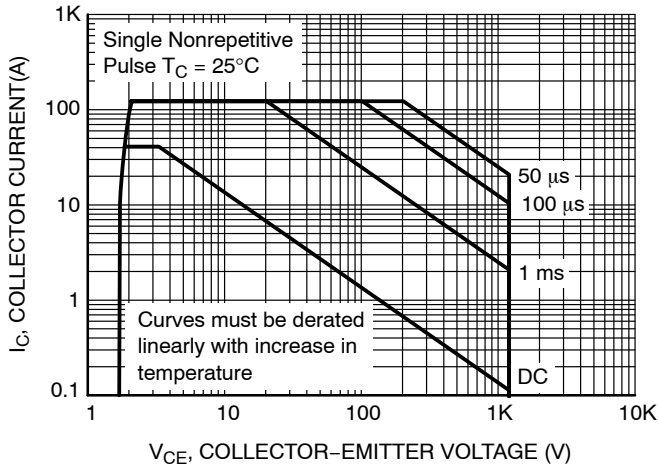


Figure 17. T1 & T2 FBSOA

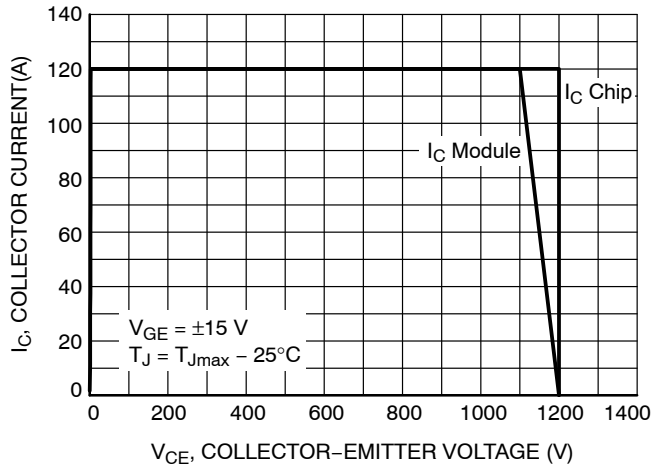


Figure 18. T1 & T2 RBSOA

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TYPICAL CHARACTERISTICS – IGBT Protection Diode and Bypass Diode

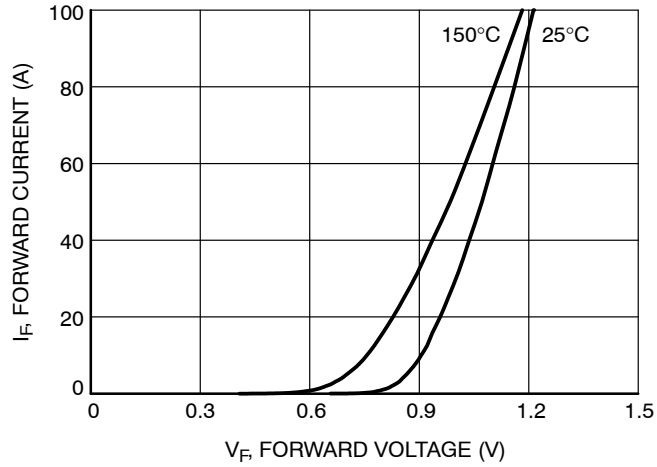


Figure 19. Diode Forward Characteristic

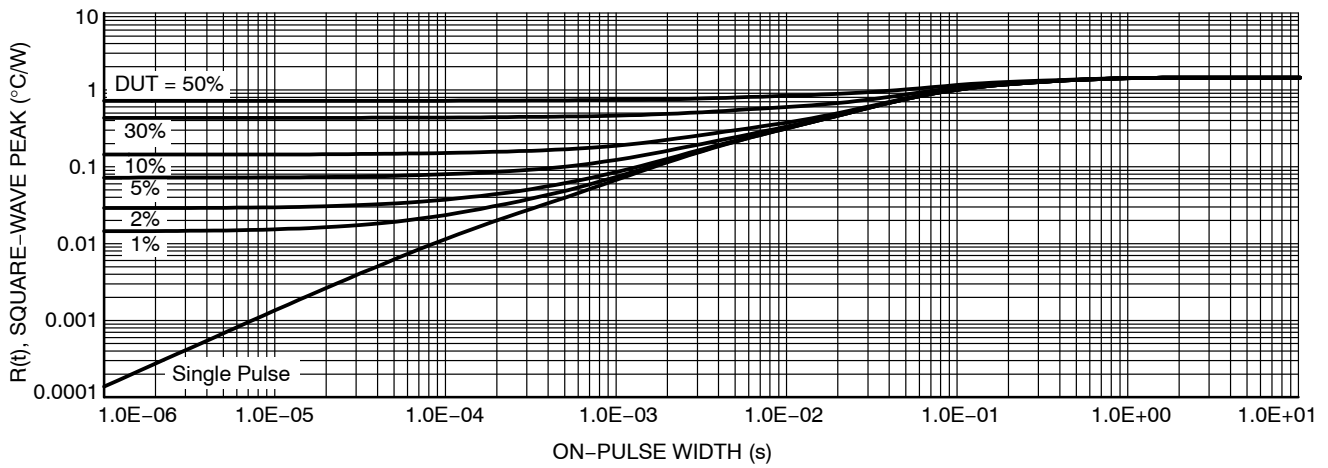


Figure 20. Diode Transient Thermal Impedance Bypass Diode / IGBT Protection Diode

TYPICAL CHARACTERISTICS – Thermistor

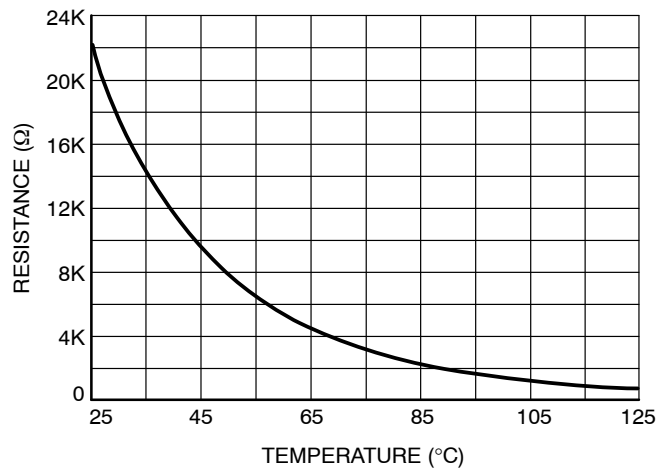


Figure 21. Thermistor Characteristic

MECHANICAL CASE OUTLINE

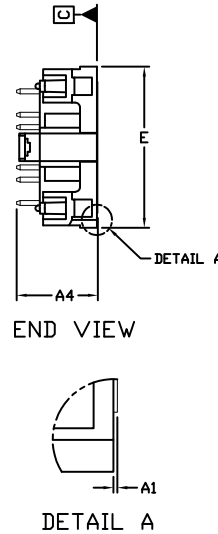
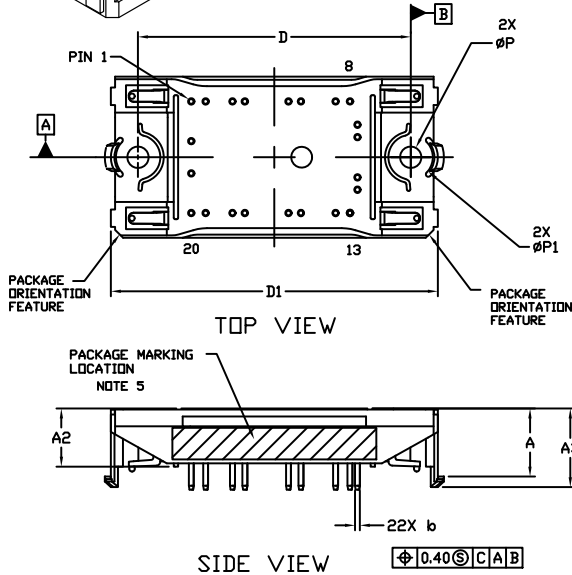
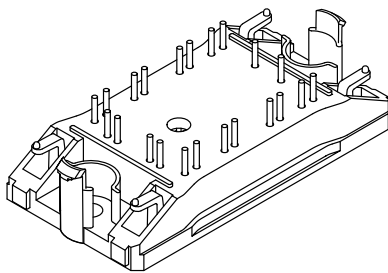
PACKAGE DIMENSIONS

ON Semiconductor®



PIM22, 55x32.5 / Q0BOOST CASE 180AJ ISSUE B

DATE 08 NOV 2017



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 1.00 AND 3.00 FROM THE TERMINAL TIP.
4. POSITION OF THE CENTER OF THE TERMINALS IS DETERMINED FROM DATUM B THE CENTER OF DIMENSION D, X DIRECTION, AND FROM DATUM A, Y DIRECTION. POSITIONAL TOLERANCE, AS NOTED IN DRAWING, APPLIES TO EACH TERMINAL IN BOTH DIRECTIONS.
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES.

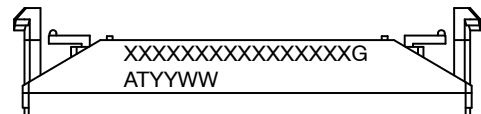
| DIM | MILLIMETERS | |
|-----|-------------|-------|
| | MIN. | NDM. |
| A | 13.50 | 13.90 |
| A1 | 0.10 | 0.30 |
| A2 | 11.50 | 11.90 |
| A3 | 15.65 | 16.05 |
| A4 | 16.35 | REF |
| b | 0.95 | 1.05 |
| D | 54.80 | 55.20 |
| D1 | 65.60 | 66.20 |
| E | 32.20 | 32.80 |
| P | 4.20 | 4.40 |
| P1 | 8.90 | 9.10 |

MOUNTING HOLE POSITION

NOTE 4

| PIN | HOLE POSITION | | PIN | PIN POSITION | | PIN | PIN POSITION | | PIN | PIN POSITION | |
|-----|---------------|--------|-----|--------------|-------|-----|--------------|-------|-----|--------------|--------|
| | X | Y | | X | Y | | X | Y | | X | Y |
| 1 | -16.75 | -11.25 | 12 | 16.75 | 6.55 | 1 | -16.75 | 11.25 | 12 | 16.75 | -6.55 |
| 2 | -13.85 | -11.25 | 13 | 15.25 | 11.25 | 2 | -13.85 | 11.25 | 13 | 15.25 | -11.25 |
| 3 | -8.45 | -11.25 | 14 | 12.35 | 11.25 | 3 | -8.45 | 11.25 | 14 | 12.35 | -11.25 |
| 4 | -5.95 | -11.25 | 15 | 5.35 | 11.25 | 4 | -5.95 | 11.25 | 15 | 5.35 | -11.25 |
| 5 | 2.85 | -11.25 | 16 | 2.85 | 11.25 | 5 | 2.85 | 11.25 | 16 | 2.85 | -11.25 |
| 6 | 5.35 | -11.25 | 17 | -5.95 | 11.25 | 6 | 5.35 | 11.25 | 17 | -5.95 | -11.25 |
| 7 | 12.35 | -11.25 | 18 | -8.45 | 11.25 | 7 | 12.35 | 11.25 | 18 | -8.45 | -11.25 |
| 8 | 15.25 | -11.25 | 19 | -13.85 | 11.25 | 8 | 15.25 | 11.25 | 19 | -13.85 | -11.25 |
| 9 | 16.75 | -6.55 | 20 | -16.75 | 11.25 | 9 | 16.75 | 6.55 | 20 | -16.75 | -11.25 |
| 10 | 16.75 | -4.05 | 21 | -16.75 | 3.25 | 10 | 16.75 | 4.05 | 21 | -16.75 | -3.25 |
| 11 | 16.75 | 4.05 | 22 | -16.75 | -3.25 | 11 | 16.75 | -4.05 | 22 | -16.75 | 3.25 |

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
 G = Pb-Free Package
 AT = Assembly & Test Site Code
 YYWW = Year and Work Week Code

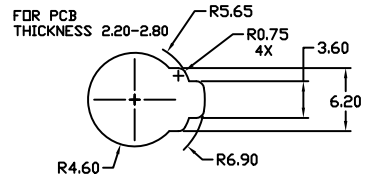
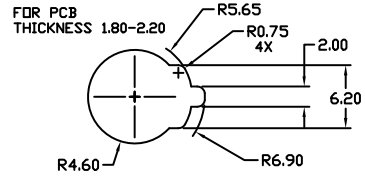
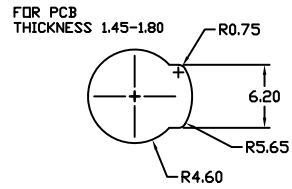
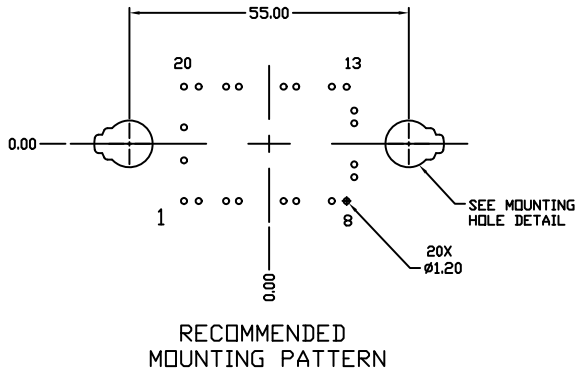
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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CASE 180AJ
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MOUNTING HOLE DETAIL

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